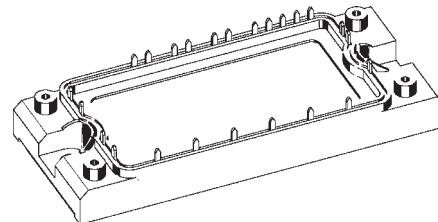
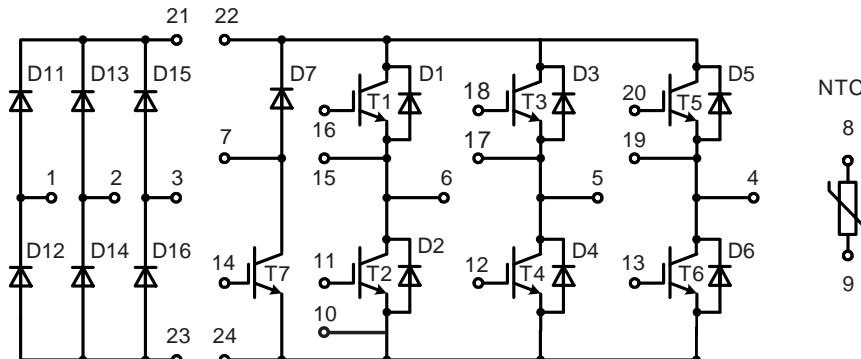


Converter - Brake - Inverter Module (CBI2)

NPT³-IGBT



Three Phase Rectifier	Brake Chopper	Three Phase Inverter
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 1200 \text{ V}$	$V_{CES} = 1200 \text{ V}$
$I_{FAVM} = 42 \text{ A}$	$I_{C25} = 35 \text{ A}$	$I_{C25} = 52 \text{ A}$
$I_{FSM} = 300 \text{ A}$	$V_{CE(sat)} = 2.3 \text{ V}$	$V_{CE(sat)} = 2.2 \text{ V}$

Input Rectifier Bridge D11 - D16

Symbol	Conditions	Maximum Ratings		
V_{RRM}		1600		V
I_{FAV}	$T_c = 80^\circ\text{C}$; sine 180°	30		A
I_{DAVM}	$T_c = 80^\circ\text{C}$; rectangular; $d = 1/3$; bridge	80		A
I_{FSM}	$T_{VJ} = 25^\circ\text{C}$; $t = 10 \text{ ms}$; sine 50 Hz	300		A
P_{tot}	$T_c = 25^\circ\text{C}$	100		W

Symbol	Conditions	Characteristic Values		
		($T_{VJ} = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.
V_F	$I_F = 35 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		1.2	1.4
			1.2	V
I_R	$V_R = V_{RRM}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		0.02	mA
			0.4	mA
R_{thJC}	(per diode)			1.3 K/W

Application: AC motor drives with

- Input from single or three phase grid
- Three phase synchronous or
- asynchronous motor
- electric braking operation

Features

- High level of integration - only one power semiconductor module required for the whole drive
- Inverter with NPT³ IGBTs
 - low saturation voltage
 - positive temperature coefficient
 - fast switching
 - short tail current
- Epitaxial free wheeling diodes with Hiperfast and soft reverse recovery
- Industry standard package with insulated copper base plate and soldering pins for PCB mounting
- Temperature sense included

Output Inverter T1 - T6

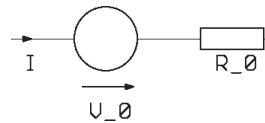
Symbol	Conditions	Maximum Ratings		
V_{CES}	$T_{VJ} = 25^\circ\text{C}$ to 150°C	1200		V
V_{GES}	Continuous	± 20		V
I_{C25}	$T_C = 25^\circ\text{C}$	52		A
I_{C80}	$T_C = 80^\circ\text{C}$	36		A
I_{CM}	RBSOA; $V_{GE} = \pm 15$ V; $R_G = 39 \Omega$; $T_{VJ} = 125^\circ\text{C}$	50		A
V_{CEK}	Clamped inductive load; $L = 100 \mu\text{H}$	V_{CES}		
t_{sc} (SCSOA)	$V_{CE} = 900$ V; $V_{GE} = \pm 15$ V; $R_G = 39 \Omega$; $T_{VJ} = 125^\circ\text{C}$ non-repetitive	10		μs
P_{tot}	$T_C = 25^\circ\text{C}$	225		W

Symbol	Conditions	Characteristic Values		
		($T_{VJ} = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.
$V_{CE(sat)}$	$I_C = 35$ A; $V_{GE} = 15$ V; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.2 2.5	2.8	V
$V_{GE(th)}$	$I_C = 1$ mA; $V_{GE} = V_{CE}$	4.5	6.5	V
I_{CES}	$V_{CE} = V_{CES}$; $V_{GE} = 0$ V; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	0.4 0.4	0.4	mA
I_{GES}	$V_{CE} = 0$ V; $V_{GE} = \pm 20$ V		200	nA
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^\circ\text{C}$ $V_{CE} = 600$ V; $I_C = 35$ A $V_{GE} = \pm 15$ V; $R_G = 39 \Omega$	150 60 700 50 4.2 3.5		ns ns ns ns mJ mJ
C_{ies}		2		nF
Q_{Gon}		250		nC
R_{thJC}	(per IGBT)		0.55	K/W

Output Inverter D1 - D6

Symbol	Conditions	Maximum Ratings		
I_{F25}	$T_C = 25^\circ\text{C}$	50		A
I_{F80}	$T_C = 80^\circ\text{C}$	33		A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 35$ A; $V_{GE} = 0$ V; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.8 1.8	V	V
t_{RM} t_{rr}	$I_F = 30$ A; $di_F/dt = -500$ A/ μs ; $T_{VJ} = 125^\circ\text{C}$ $V_R = 600$ V; $V_{GE} = 0$ V	27 150		A ns
R_{thJC}			1.19	K/W

Equivalent Circuits for Simulation**Conduction****D11 - D16**

Rectifier Diode (typ. at $T_J = 125^\circ\text{C}$)
 $V_o = 0.83$ V; $R_o = 11$ m Ω

T1 - T6 / D1 - D6

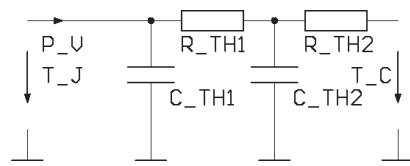
IGBT (typ. at $V_{GE} = 15$ V; $T_J = 125^\circ\text{C}$)
 $V_o = 0.95$ V; $R_o = 45$ m Ω

Free Wheeling Diode (typ. at $T_J = 125^\circ\text{C}$)
 $V_o = 1.26$ V; $R_o = 15$ m Ω

T7 / D7

IGBT (typ. at $V_{GE} = 15$ V; $T_J = 125^\circ\text{C}$)
 $V_o = 1.37$ V; $R_o = 62$ m Ω

Free Wheeling Diode (typ. at $T_J = 125^\circ\text{C}$)
 $V_o = 1.39$ V; $R_o = 56$ m Ω

Thermal Response**D11 - D16**

Rectifier Diode (typ.)
 $C_{th1} = 0.106$ J/K; $R_{th1} = 1.06$ K/W
 $C_{th2} = 0.79$ J/K; $R_{th2} = 0.239$ K/W

T1 - T6 / D1 - D6

IGBT (typ.)
 $C_{th1} = 0.201$ J/K; $R_{th1} = 0.419$ K/W
 $C_{th2} = 1.25$ J/K; $R_{th2} = 0.131$ K/W

Free Wheeling Diode (typ.)
 $C_{th1} = 0.116$ J/K; $R_{th1} = 0.973$ K/W
 $C_{th2} = 0.879$ J/K; $R_{th2} = 0.217$ K/W

T7 / D7

IGBT (typ.)
 $C_{th1} = 0.156$ J/K; $R_{th1} = 0.545$ K/W
 $C_{th2} = 1.162$ J/K; $R_{th2} = 0.155$ K/W

Free Wheeling Diode (typ.)
 $C_{th1} = 0.043$ J/K; $R_{th1} = 2.738$ K/W
 $C_{th2} = 0.54$ J/K; $R_{th2} = 0.462$ K/W

Brake Chopper T7

Symbol	Conditions	Maximum Ratings		
V_{CES}	$T_{VJ} = 25^\circ\text{C}$ to 150°C	1200		V
V_{GES}	Continuous	± 20		V
V_{GEM}	Transient	± 30		V
I_{C25}	$T_C = 25^\circ\text{C}$	35		A
I_{C80}	$T_C = 80^\circ\text{C}$	25		A
I_{CM}	RBSOA; $V_{GE} = \pm 15$ V; $R_G = 82 \Omega$; $T_{VJ} = 125^\circ\text{C}$	35		A
V_{CEK}	Clamped inductive load; $L = 100 \mu\text{H}$	V_{CES}		
t_{SC} (SCSOA)	$V_{CE} = V_{CES}$; $V_{GE} = \pm 15$ V; $R_G = 82 \Omega$; $T_{VJ} = 125^\circ\text{C}$ non-repetitive	10		μs
P_{tot}	$T_C = 25^\circ\text{C}$	180		W

Symbol	Conditions	Characteristic Values		
		($T_{VJ} = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.
$V_{CE(sat)}$	$I_C = 20$ A; $V_{GE} = 15$ V; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.3 2.6	3 V	V
$V_{GE(th)}$	$I_C = 0.6$ mA; $V_{GE} = V_{CE}$	4.5	6.5	V
I_{CES}	$V_{CE} = V_{CES}$; $V_{GE} = 0$ V; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	0.8	0.8	mA mA
I_{GES}	$V_{CE} = 0$ V; $V_{GE} = \pm 20$ V		200	nA
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^\circ\text{C}$ $V_{CE} = 600$ V; $I_C = 20$ A $V_{GE} = \pm 15$ V; $R_G = 82 \Omega$	100 75 500 70 3.1 2.4	ns ns ns ns mJ mJ	
C_{ies} Q_{Gon}	$V_{CE} = 25$ V; $V_{GE} = 0$ V; $f = 1$ MHz $V_{CE} = 600$ V; $V_{GE} = 15$ V; $I_C = 20$ A	1000 70	pF nC	
R_{thJC}			0.7	K/W

Brake Chopper D7

Symbol	Conditions	Maximum Ratings		
V_{RRM}	$T_{VJ} = 25^\circ\text{C}$ to 150°C	1200		V
I_{F25}	$T_C = 25^\circ\text{C}$	16		A
I_{F80}	$T_C = 80^\circ\text{C}$	11		A
Symbol	Conditions	Characteristic Values		
Symbol	Conditions	min.	typ.	max.
V_F	$I_F = 20$ A; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.6	3.6 V	V
I_R	$V_R = V_{RRM}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	0.07	0.06 mA	mA
I_{RM} t_{rr}	$I_F = 20$ A; $di_F/dt = -400$ A/ μs ; $T_{VJ} = 125^\circ\text{C}$ $V_R = 600$ V	13 110	A ns	
R_{thJC}			3.2	K/W

Temperature Sensor NTC

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
R_{25}	T = 25°C	4.75	5.0	5.25 kΩ
$B_{25/50}$			3375	K

Module

Symbol	Conditions	Maximum Ratings	
T_{VJ}		-40...+150	°C
T_{JM}		150	°C
T_{stg}		-40...+125	°C
V_{ISOL}	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$	2500	V~
M_d	Mounting torque (M5)	2.7 - 3.3	Nm

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{\text{pin-chip}}$			5	mΩ
d_s	Creepage distance on surface	6		mm
d_A	Strike distance in air	6		mm
R_{thCH}	with heatsink compound		0.02	K/W
Weight			180	g

Dimensions in mm (1 mm = 0.0394")

